IN THE TITLE

Change the title wherever it appears to read as follows:

--Nitride Semiconductor Device with Improved Lifetime and High Output Power--.

IN THE ABSTRACT

Insert the attached Abstract after the claims pages. A marked-up Abstract is also attached.

IN THE CLAIMS

Cancel claims 1 and 16.

Please substitute the following amended claims for corresponding claims previously presented. A copy of the amended claims showing current revisions is attached.

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3. (Amended) The nitride semiconductor device according to Claim 1~~6~~, wherein said active layer has L ($L \geqq 2$) barrier layers so that the barrier layer arranged in a position nearest to said n-type nitride semiconductor layer is denoted as barrier layer B_1 and the i-th barrier layer (i=1, 2, 3, ...L) counted from the barrier layer B_1 toward said p-type nitride semiconductor layer is denoted as barrier layer B_i; and barrier layers B_i from i=1 to i=n ($1 < n < L$) include an n-type impurity.

4. (Amended) The nitride semiconductor device according to Claim 1~~6~~, wherein the entire barrier layers other than said first barrier layer include an n-type impurity.

5. (Amended) The nitride semiconductor device according to Claim 24, wherein said first barrier layer is arranged in the outermost position in said active layer.

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6. (Amended) The nitride semiconductor device according to Claim 24, wherein said second barrier layer is arranged in the outermost position close to said n-type nitride semiconductor layer within said active layer.

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9. (Amended) The nitride semiconductor device according to Claim 24, wherein at least one well layer within said active layer has a film thickness of not less than 40 Å.

10. (Amended) The nitride semiconductor device according to Claim 24, wherein said first barrier layer has a p-type impurity.

11. (Amended) The nitride semiconductor device according to Claim 24, wherein said first barrier layer includes a p-type impurity in the range of no less than 5×10^{16} cm^{-3} and no more than 1×10^{19} cm^{-3}.

12. (Amended) The nitride semiconductor device according to Claim 24, wherein said first barrier layer is p-type or i-type.

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14. (Amended) The nitride semiconductor device according to Claim 24, wherein said n-type nitride semiconductor layer, said active layer and said p-type nitride semiconductor layer are layered in sequence.

15. (Amended) The nitride semiconductor device according to Claim 24,

wherein said p-type nitride semiconductor layer has an upper clad layer made of a nitride semiconductor that includes Al of which the average mixed crystal ratio x is in the range of $0 < x \leq 0.05$;

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said n-type nitride semiconductor layer has a lower clad layer made of a nitride semiconductor that includes Al of which the average mixed crystal ratio x is in the range of $0 < x \leq 0.05$; and

the nitride semiconductor device has a laser device structure.

16. ~~17.~~ (Amended) The nitride semiconductor device according to Claim ~~24~~ 1, wherein said first p-type nitride semiconductor layer is provided so as to contact a barrier layer nearest to said p-type nitride semiconductor layer and has been grown being doped with a p-type impurity of which concentration is higher than that of said barrier layer in said active layer.

17. ~~18.~~ (Amended) The nitride semiconductor device according to Claim ~~24~~ 1, wherein the number of well layers in said active layer is from 1 to 3.

18. ~~19.~~ (Amended) The nitride semiconductor device according to claim ~~24~~ 1, in said active layer said second barrier layer is arranged between well layers and the film thickness ratio Rt (= [film thickness of a well layer] / [film thickness of a barrier layer]) of said well layer to the second barrier layer is in the range of $0.5 \leq Rt \leq 3$.

19. ~~20.~~ (Amended) The nitride semiconductor device according to claim ~~24~~ 1, wherein the film thickness dw of said well layer is in the range of $40 \text{ Å} \leq dw \leq 100 \text{ Å}$ while the film thickness db of said second barrier layer is in the range of $db \geq 40 \text{ Å}$.

20. ~~21.~~ (Amended) The nitride semiconductor device according to Claim ~~24~~ 1, wherein said p-type nitride semiconductor layer has an upper clad layer made of a nitride semiconductor that includes Al and said n-type nitride semiconductor layer has a lower

clad layer made of a nitride semiconductor, wherein the average mixed crystal ratio of Al in the upper clad layer is greater than that of the lower clad layer.

22. ~~23~~. (Amended) The nitride semiconductor device according to Claim ~~24~~ 1,

wherein said active layer has a well layer of which distance dB from the first p-type nitride semiconductor layer is in the range of no less than 100 Å and no more than 400 Å and has a first barrier layer within the distance dB.

Add the following new claim:

1. ~~24~~. (new) A nitride semiconductor device wherein an active layer is sandwiched between p-type nitride semiconductor layers and n-type nitride semiconductor layers,

wherein said p-type nitride semiconductor layers has an electrons confining layer adjoining said active layer and made of nitride semiconductor that includes Al;

and said active layer has a quantum well structure including at least one well layer made of nitride semiconductor that includes In and barrier layers made of nitride semiconductor, wherein a first barrier layer arranged in the nearest position to said p-type nitride semiconductor layer among said barrier layers substantially does not have an n-type impurity, while a second barrier layer that is different from said first barrier layer has an n-type impurity.--